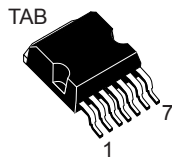
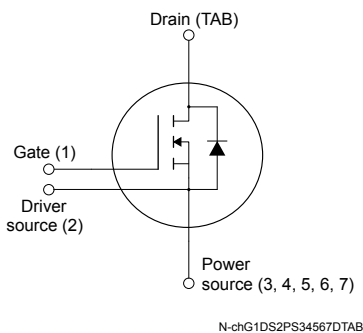


Automotive-grade silicon carbide Power MOSFET 1200 V, 19.2 mΩ typ., 90 A in an H²PAK-7 package




H²PAK-7



Features

Order code	V _{DS}	R _{DS(on)} typ.	I _D
SCT019H120G3AG	1200 V	19.2 mΩ	90 A

- AEC-Q101 qualified 
- Very low R_{DS(on)} over the entire temperature range
- High speed switching performances
- Very fast and robust intrinsic body diode
- Source sensing pin for increased efficiency

Applications

- DC/DC converter for EV/HEV
- Main inverter (electric traction)
- On board charger (OBC)

Description

This silicon carbide Power MOSFET device has been developed using ST's advanced and innovative 3rd generation SiC MOSFET technology. The device features a very low R_{DS(on)} over the entire temperature range combined with low capacitances and very high switching operations, which improve application performance in frequency, energy efficiency, system size and weight reduction.

Product status link

[SCT019H120G3AG](#)

Product summary

Order code	SCT019H120G3AG
Marking	19H120G3AG
Package	H ² PAK-7
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	1200	V
V_{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operating values)	-5 to 18	
	Gate-source transient voltage, $t_p < 1 \mu s$, $t \leq 10$ hours over lifetime	-11 to 25	
I_D	Drain current (continuous) at $T_C = 25 \text{ }^\circ\text{C}$	90	A
	Drain current (continuous) at $T_C = 100 \text{ }^\circ\text{C}$	77	
$I_{DM}^{(1)}$	Drain current (pulsed)	306	A
P_{TOT}	Total power dissipation at $T_C = 25 \text{ }^\circ\text{C}$	500	W
T_{stg}	Storage temperature range	-55 to 175	$^\circ\text{C}$
T_J	Operating junction temperature range		$^\circ\text{C}$

1. Pulse width is limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.30	$^\circ\text{C/W}$
R_{thJA}	Thermal resistance, junction-to-ambient	50	$^\circ\text{C/W}$

2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 1200\text{ V}$			10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = -10\text{ to }22\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 10\text{ mA}$	1.8	3.0	4.2	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 15\text{ V}, I_D = 40\text{ A}$		21.3		m Ω
		$V_{GS} = 18\text{ V}, I_D = 40\text{ A}$		19.2	26	
		$V_{GS} = 18\text{ V}, I_D = 40\text{ A}, T_J = 175\text{ }^\circ\text{C}$		36.5		

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 800\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	2789	-	pF
C_{oss}	Output capacitance		-	141	-	pF
C_{riss}	Reverse transfer capacitance		-	16.5	-	pF
Q_g	Total gate charge	$V_{DD} = 800\text{ V}, V_{GS} = -5\text{ to }18\text{ V}, I_D = 40\text{ A}$	-	111.2	-	nC
Q_{gs}	Gate-source charge		-	31.1	-	nC
Q_{gd}	Gate-drain charge		-	38.3	-	nC
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0\text{ A}$	-	1.5	-	Ω

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	$V_{DD} = 800\text{ V}, I_D = 40\text{ A},$	-	449	-	μJ
E_{off}	Turn-off switching energy	$R_G = 3.3\text{ }\Omega, V_{GS} = -5\text{ to }18\text{ V}$	-	246	-	μJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 800\text{ V}, I_D = 40\text{ A},$ $R_G = 3.3\text{ }\Omega, V_{GS} = -5\text{ to }18\text{ V}$	-	18.4	-	ns
t_r	Rise time		-	7.7	-	ns
$t_{d(off)}$	Turn-off delay time		-	36.6	-	ns
t_f	Fall time		-	17	-	ns

Table 7. Reverse SiC diode characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Continuous diode forward current	$T_C = 25\text{ }^\circ\text{C}$	-		90	A
		$T_C = 100\text{ }^\circ\text{C}$	-		77	
V_{SD}	Diode forward voltage	$I_{SD} = 40\text{ A}$, $V_{GS} = 0\text{ V}$	-	3		V
t_{rr}	Reverse recovery time	$I_{SD} = 40\text{ A}$, $di/dt = 1000\text{ A}/\mu\text{s}$, $V_{DD} = 800\text{ V}$, $V_{GS} = -5\text{ V}$	-	20.8		ns
Q_{rr}	Reverse recovery charge		-	152		nC
I_{RRM}	Reverse recovery current		-	12.1		A

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

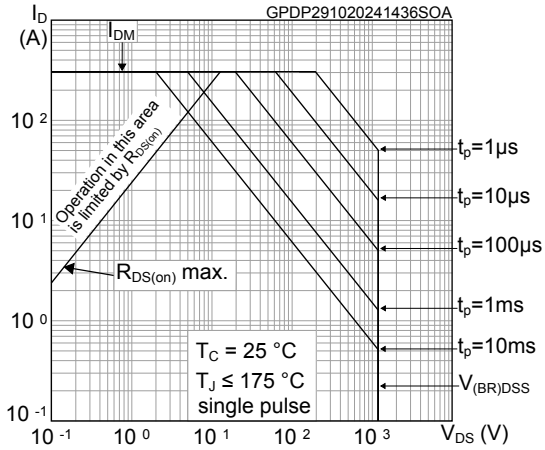


Figure 2. Maximum transient thermal impedance

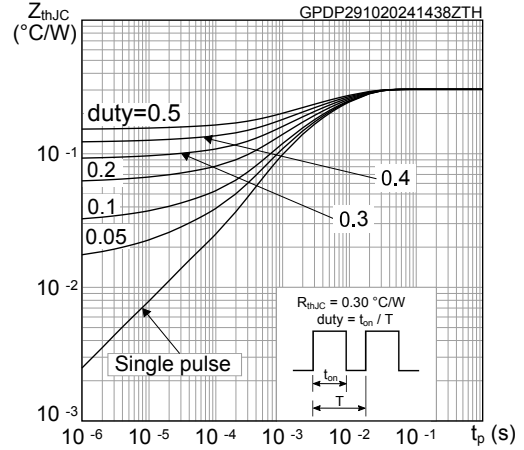


Figure 3. Typical output characteristics ($T_J = 25\text{ °C}$)

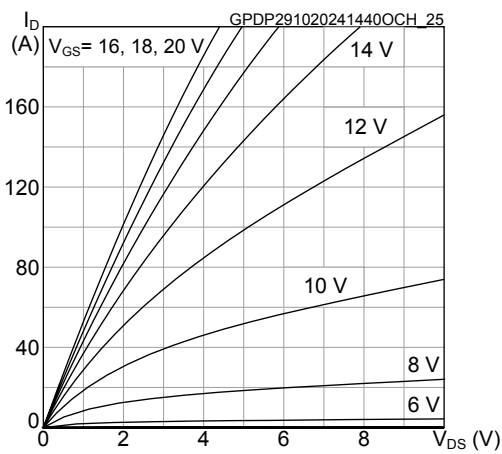


Figure 4. Typical output characteristics ($T_J = 175\text{ °C}$)

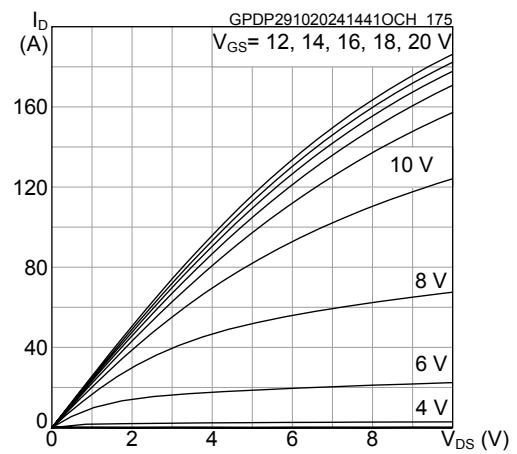


Figure 5. Typical transfer characteristics

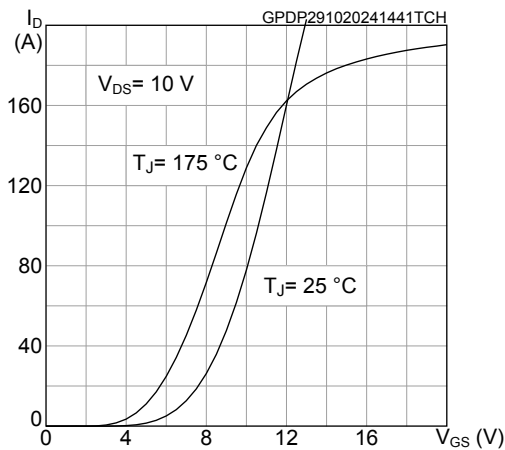


Figure 6. Total power dissipation

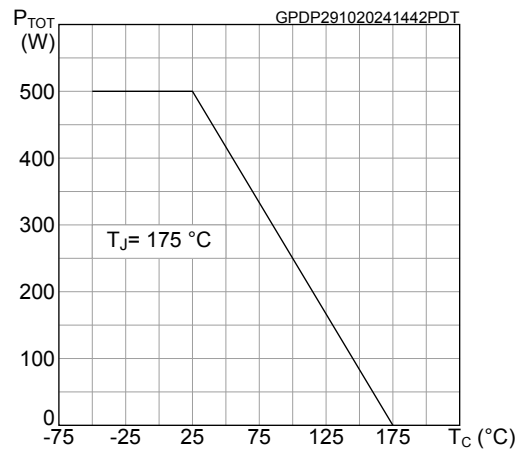


Figure 7. Typical gate charge characteristics

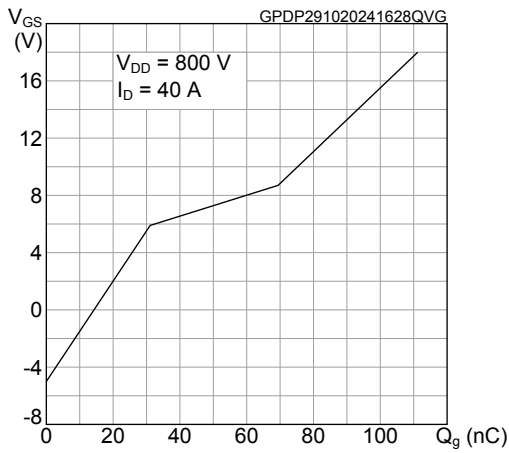


Figure 8. Typical capacitance characteristics

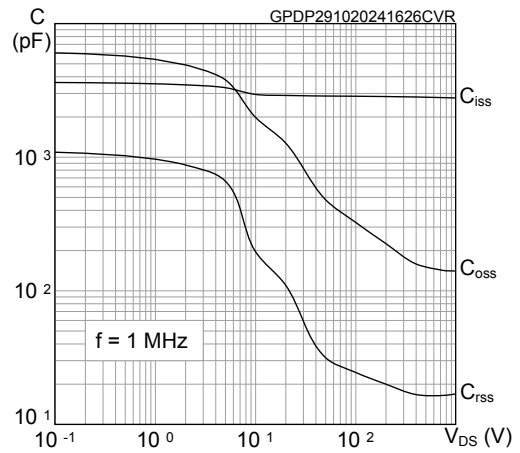


Figure 9. Typical switching energy vs drain current

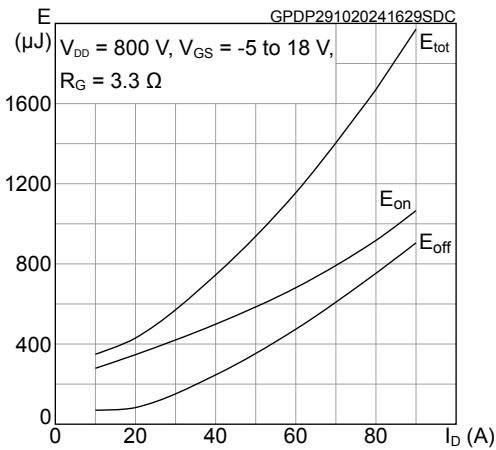


Figure 10. Typical switching energy vs supply voltage

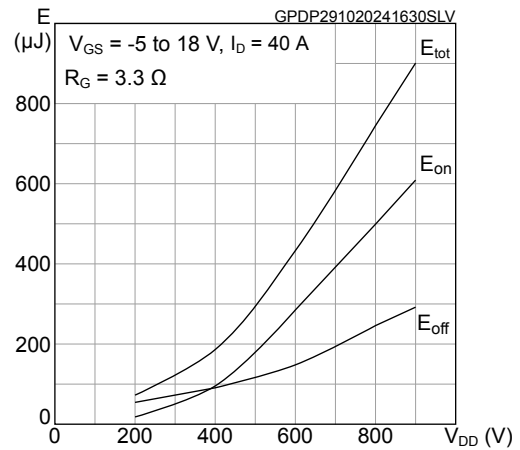


Figure 11. Typical switching energy vs gate resistance

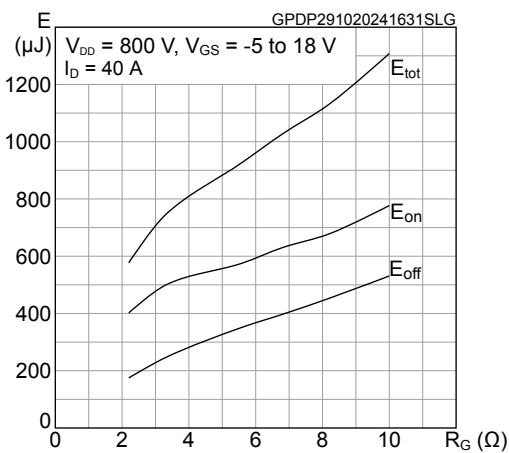


Figure 12. Typical switching energy vs temperature

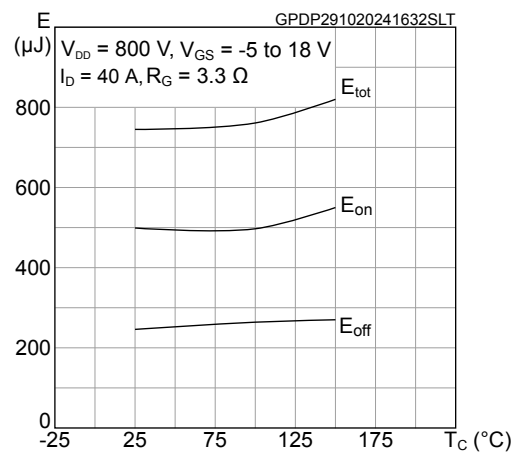


Figure 13. Normalized breakdown voltage vs temperature

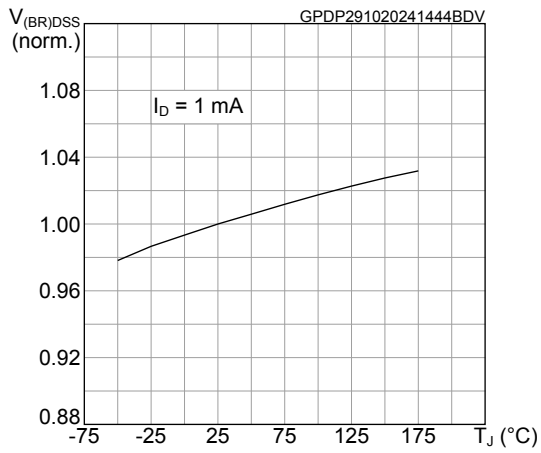


Figure 14. Normalized gate threshold vs temperature

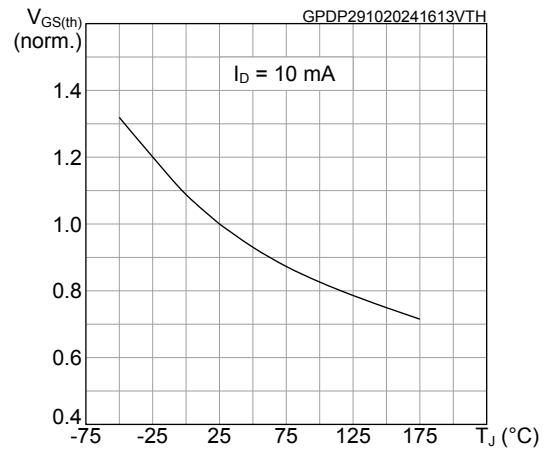


Figure 15. Normalized on-resistance vs temperature

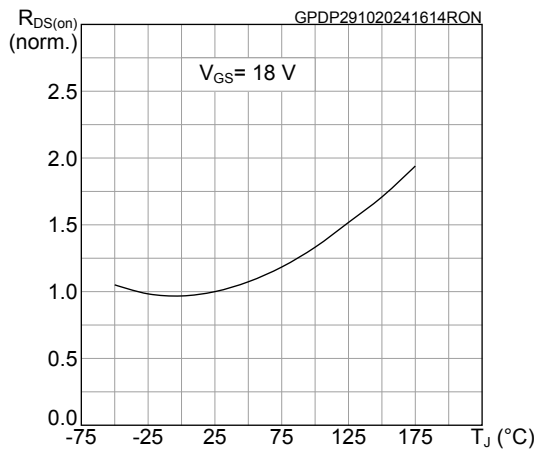


Figure 16. Typical reverse conduction characteristics ($T_J = 25^\circ\text{C}$)

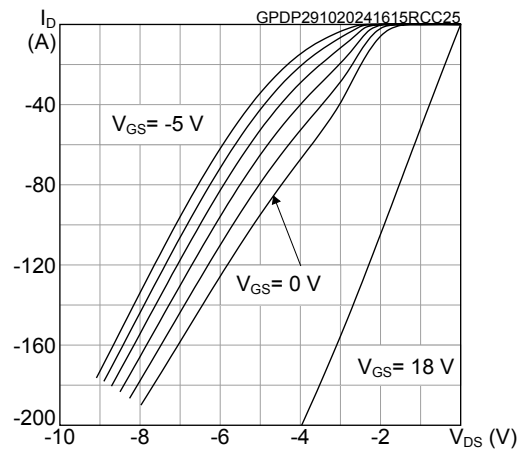
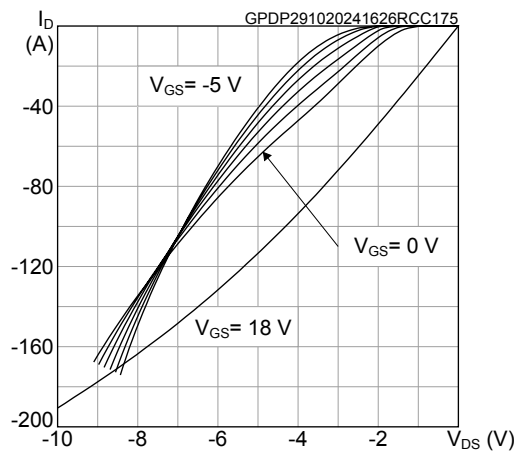


Figure 17. Typical reverse conduction characteristics ($T_J = 175^\circ\text{C}$)

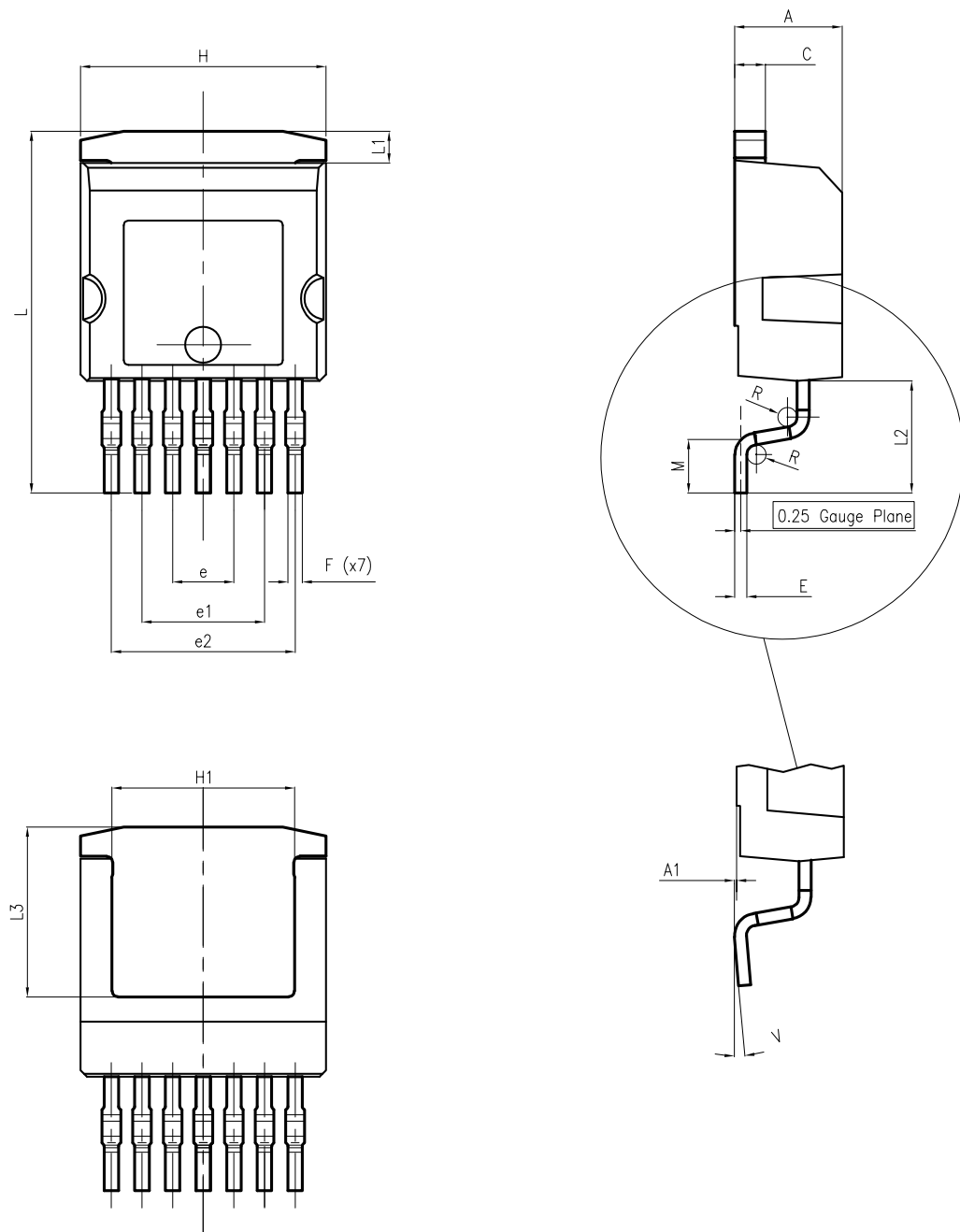


3 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 H²PAK-7 package information

Figure 18. H²PAK-7 package outline

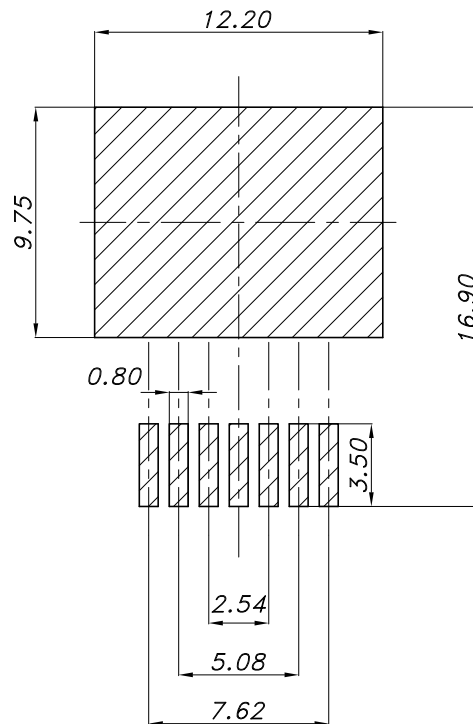


DM00249216_6

Table 8. H²PAK-7 package mechanical data

Dim.	mm	
	Min.	Max.
A	4.30	4.80
A1	0.03	0.20
C	1.17	1.37
e	2.34	2.74
e1	4.88	5.28
e2	7.42	7.82
E	0.45	0.60
F	0.50	0.70
H	10.00	10.40
H1	7.40	8.00
L	14.75	15.25
L1	1.27	1.40
L2	4.35	4.95
L3	6.85	7.25
M	1.90	2.50
R	0.20	0.60
V	0°	8°

Figure 19. H²PAK-7 recommended footprint

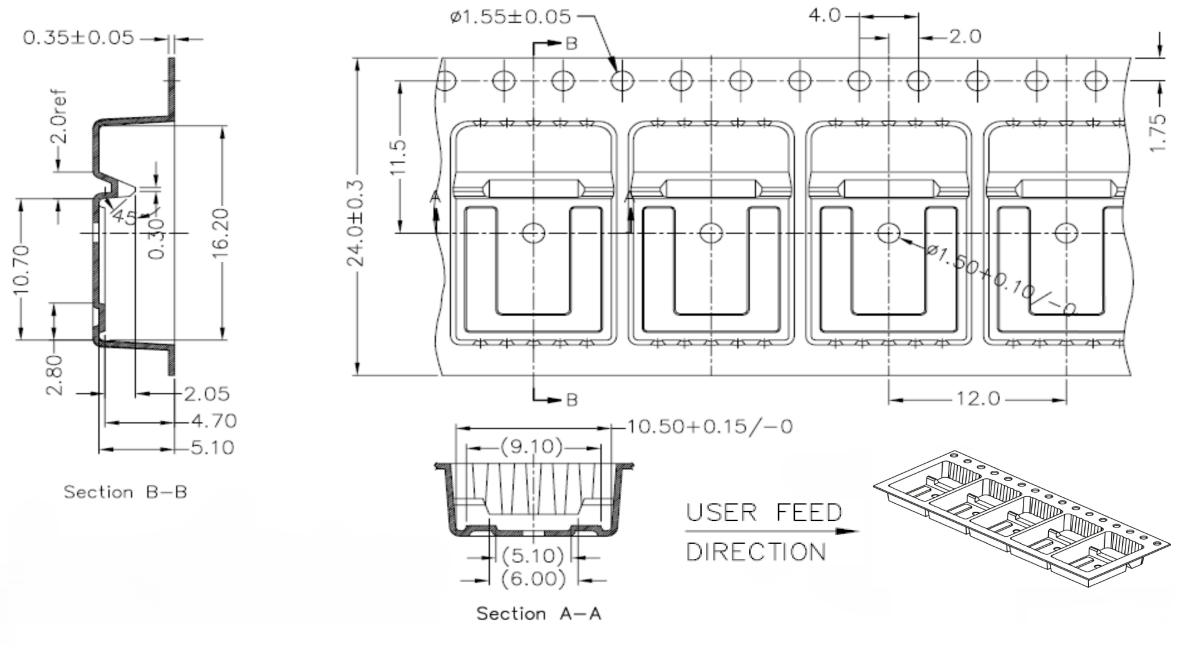


footprint_DM00249216_6

Note: Dimensions are in mm.

3.2 H²PAK packing information

Figure 20. H²PAK tape drawing (dimensions are in mm)



0079900_14

Revision history

Table 9. Document revision history

Date	Revision	Changes
30-Jun-2025	1	First release.

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